

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2487	257/469,536,543,607,E29.326.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 07:49
L2	7605	257/154,350,358,359,363,379-381,516,533, 536-543,571,572,577,580-582,904.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 07:50
L3	8353	1 or 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 07:51
L4	2	3 and ((ion near implant\$5) with (crystalline near silicon near substrate) with (room near temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:00
L5	11	3 and ((ion near implant\$5) with (crystalline near silicon near substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:00
L6	3957027	resist\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:17
L7	2	6 and ((ion near implant\$5) with (crystalline near silicon near substrate) with (room near temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:52
L8	73	6 and ((ion near implant\$5) with (crystalline near silicon near substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:00
L9	197180	resist\$4 near (element\$1 member\$1 structure\$1 device\$1 component\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:18

L10	3	9 and ((ion near implant\$5) with (silicon near substrate) with (room near temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:20
L11	10	9 and ((ion near implant\$5) with substrate with (room near temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:59
L12	22	("4178674" "4367580" "4466081" "4961103" "5017979" "5037766" "5053849" "5101250" "5126809" "5130264" "5147813" "5168075" "5204276" "5229631" "5231041" "5349494" "5364805" "5434438" "5464998" "5506737" "5565371" "6124168").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 08:30
L13	4	("4961103" "5037766" "5349494" "5793097").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/16 08:37
L14	156	((ion near implant\$5) and (crystalline near silicon near substrate) and (room near temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:52
L15	126	14 and resist\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 09:10
L16	2480	9 and ((ion near implant\$5) with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 08:58
L17	262	16 and (room near temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 09:08
L18	66	17 and ((PN P/N NP N/P (P near N)) near junction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 09:08

L19	1630	16 and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 09:08
L20	510	19 and ((PN P/N NP N/P (P near N)) near junction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 09:08
L21	45	20 and (resist\$4 with arsenic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/09/16 09:11